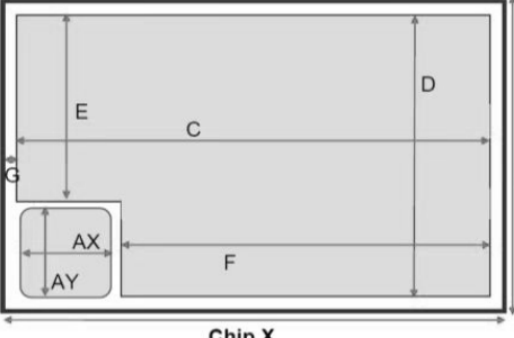
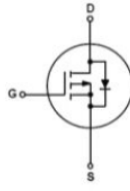



Pad Information		Project	Size(um)
		Chip X (in S/L)	1390
		Chip Y (in S/L)	820
		Scribe line	60
		AX	140
		AY	140
		C	1245
		D	675
		E	535
		F	1100
G	72.5		
Die Size	1390 um X 820 um (with S/L)	Symbol	Die Outline
Gross Die	25000EA		
Wafer Diameter	200 mm		
Wafer Thickness	6 mil ± 0.5 mil		
Material of Electrode	Front : Al (Thickness : 45 KÅ ± 3 KÅ) Back : Ti-Ni-Ag		
Width of Scribe Line	60um		

3, Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)

Symbol	Parameter	Rating				Unit
V _{DS}	Drain-Source Voltage	-100				V
V _{GSS}	Gate-Source Voltage	±20				V
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _{DS} = -250 μA	-1.3	-1.8	-2.5	V
I _{DSS}	Drain Leakage Current	V _{DS} = -100 V, V _{GS} = 0 V	-	-	-1	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ± 20 V, V _{DS} = 0 V	-	-	± 100	nA
R _{DS(ON)②}	On-State Resistance	V _{GS} = -10 V, I _{DS} = -1 A		260	320	mΩ
		V _{GS} = -4.5 V, I _{DS} = -1 A		290	380	
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _{SD} = -0.5 A, V _{GS} = 0 V	-	-0.7	-1.3	V

Notes: ① This characteristics assumes the die are assembled in SOT23 packages. Actual performance may degrade when assembled.

② CP measured on wafer by probe card.